Silicon N-Channel MOS FET

# HITACHI

ADE-208-1302 (Z) 1st. Edition Mar. 2001

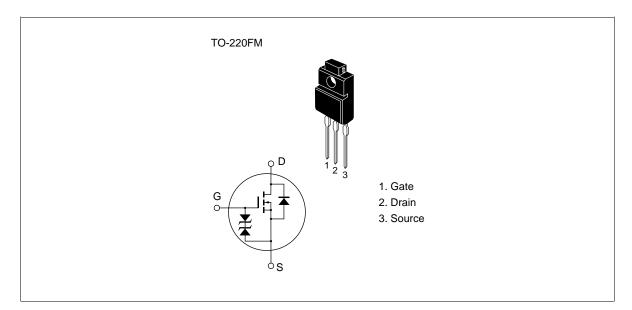
## Application

High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

### Outline





# Absolute Maximum Ratings (Ta = $25^{\circ}$ C)

| Item                        |                 | Symbol           | Ratings     | Unit |
|-----------------------------|-----------------|------------------|-------------|------|
| Drain to source voltage     | 2SK1626         | V <sub>DSS</sub> | 450         | V    |
|                             | 2SK1627         |                  | 500         |      |
| Gate to source voltage      |                 | V <sub>GSS</sub> | ±30         | V    |
| Drain current               |                 | I <sub>D</sub>   | 5           | A    |
| Drain peak current          |                 | L *1<br>D(pulse) | 20          | A    |
| Body to drain diode reverse | e drain current | I <sub>DR</sub>  | 5           | A    |
| Channel dissipation         |                 | Pch*2            | 35          | W    |
| Channel temperature         |                 | Tch              | 150         | °C   |
| Storage temperature         |                 | Tstg             | -55 to +150 | °C   |

Note 1. PW 10 µs, duty cycle 1%

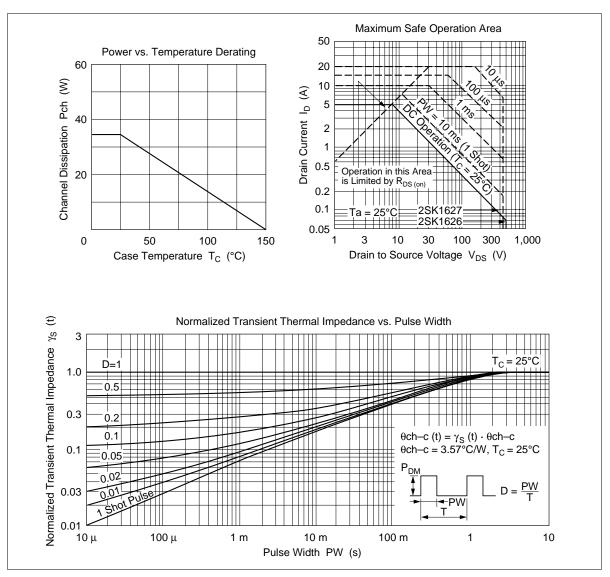
2. Value at  $T_c = 25^{\circ}C$ 

## **Electrical Characteristics** (Ta = 25°C)

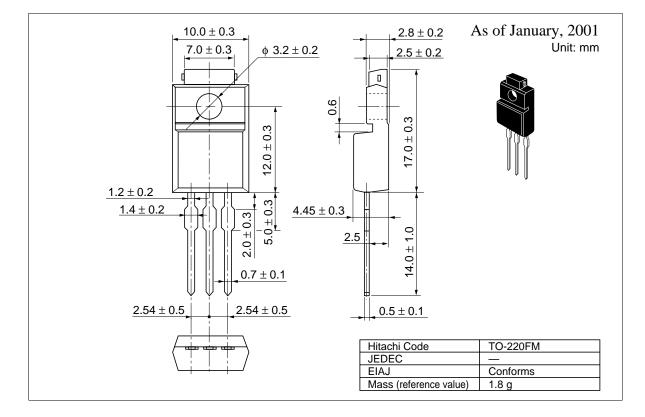
| Item                                      |           | Symbol                      | Min | Тур  | Max | Unit | Test conditions   |
|---|-----------|-----------------------------|-----|------|-----|------|---|
| Drain to source                           | 2SK1626   | $V_{(BR)DSS}$               | 450 | _    | _   | V    | $I_{\rm D} = 10$ mA, $V_{\rm GS} = 0$                                     |
| breakdown voltage                         | 2SK1627   | -                           | 500 | =    |     |      |   |
| Gate to source breakdown voltage          |           | $V_{(\text{BR})\text{GSS}}$ | ±30 | _    | _   | V    | $I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$                                   |
| Gate to source leak current               |           | I <sub>GSS</sub>            | —   | —    | ±10 | μA   | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$                                   |
| Zero gate voltage                         | 2SK1626   | I <sub>DSS</sub>            | —   | —    | 250 | μA   | $V_{\rm DS} = 360 \ V, \ V_{\rm GS} = 0$                                  |
| drain current                             | 2SK1627   | -                           |     |      |     |      | $V_{\rm DS} = 400 \ V, \ V_{\rm GS} = 0$                                  |
| Gate to source cutoff voltage             |           | $V_{\text{GS(off)}}$        | 2.0 | —    | 3.0 | V    | $I_{\rm D}$ = 1 mA, $V_{\rm DS}$ = 10 V                                   |
| Static Drain to source                    | e 2SK1626 | $R_{DS(on)}$                | _   | 1.0  | 1.4 |      | $I_{\rm D} = 2.5 \text{ A}, \text{ V}_{\rm GS} = 10 \text{ V}^{*1}$       |
| on state resistance                       | 2SK1627   | -                           | —   | 1.2  | 1.5 | _    |   |
| Forward transfer adm                      | nittance  | yfs                         | 2.5 | 4.0  | —   | S    | $I_{\rm D}$ = 2.5 A, $V_{\rm DS}$ = 10 V * <sup>1</sup>                   |
| Input capacitance                         |           | Ciss                        |     | 640  |     | pF   | $V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0,$                              |
| Output capacitance                        |           | Coss                        | _   | 160  | _   | pF   | f = 1 MHz   |
| Reverse transfer capacitance              |           | Crss                        | _   | 20   | _   | pF   |   |
| Turn-on delay time                        |           | $\mathbf{t}_{d(on)}$        | _   | 10   | _   | ns   | $I_{\rm D} = 2.5 \text{ A}, V_{\rm GS} = 10 \text{ V},$                   |
| Rise time                                 |           | t,                          | _   | 25   | _   | ns   | R <sub>L</sub> = 12   |
| Turn-off delay time                       |           | $t_{d(off)}$                | —   | 50   | —   | ns   |   |
| Fall time                                 |           | t <sub>f</sub>              | _   | 30   | _   | ns   |   |
| Body to drain diode for voltage           | orward    | $V_{DF}$                    | _   | 0.95 | _   | V    | $I_{F} = 5 \text{ A}, V_{GS} = 0$   |
| Body to drain diode reverse recovery time |           | t <sub>rr</sub>             | _   | 300  | _   | ns   | $I_F = 5 \text{ A}, V_{GS} = 0,$<br>$di_F/dt = 100 \text{ A/}\mu\text{s}$ |
| Note 1 Pulse test                         | t         |                             |     |      |     |      |   |

Note 1. Pulse test

See characteristic curves of 2SK1155, 2SK1156.



### **Package Dimensions**



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